M any body e ects in nite m etallic carbon nanotubes.

¹ Instituto de Ciencia de Materiales de Madrid. CSIC. Cantoblanco. 28049 Madrid. Spain and ²Department of Physics. Boston University. 590 Commonwealth Avenue, Boston, Massachusetts 02215, USA

The non hom ogeneity of the charge distribution in a carbon nanotube leads to the form ation of an excitonic resonance, in a similar way to the one observed in X-ray absorption in m etals. As a result, a positive anomally at low bias appears in the tunnelling density of states. This excit depends on the screening of the electron (electron interactions by m etallic gates, and it m odi ex the coupling of the nanotube to normal and superconducting electrodes.

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Introduction. The addition of single electrons to nite carbon nanotubes induces measurable e ects, related to the nite spacing between the energy levels and to the electrostatic energy associated to the electron charge[1, 2, 3, 4, 5, 6, 7, 8, 9]The standard model for Coulomb blockade[10, 11] assumes that the electrostatic potential inside the system is raised by the addition of an individual electron, preventing tunnelling unless di erent charge states are degenerate. The potential is supposed to be constant throughout the sam ple. When it is not the case, non equilibrium e ects m ay occur[12, 13], w hich are related to the Ferm i edge singularities associated to the sudden ejection of a core electron in a metal[14]. One dim ensional systems, like the nanotubes, are good candidates for observing these e ects, as screening is suppressed, and the electrostatic potential inside them can be m odulated by m etallic gates in their proxim ity. O ther e ects related to modulations in the electrostatic potentialwere considered in [15].

We calculate in this paper the changes in the tunnelling density of states due to the non hom ogeneity of the electrostatic potential, for dierent possible experimental setups. The eects discussed here look similar, but are different from the Luttinger liquid features expected near a contact [16, 17, 18, 19], which have also been observed in nanotubes [20, 21].

The next section describes the model to be studied. The main results are presented next. Then, we analyze how to incorporate Luttinger liquid e ects. The expected behavior at energies comparable to the spacing between individual electronic levels is discussed next. The paper concludes with a section on possible experimental consequences of the e ects analyzed here.

The model. We consider only a nearest neighbor hopping, t, between orbitals at the C atoms. Each subband in a zigzag nanotube can be modelled by a one dimensional tight binding ham iltonian with two sites per unit cell and two dierent hoppings, t and t(1 + e^{i_n}) = $2te^{i_n=2}\cos(n=2)$, where n=(2n)=N; n=1; ;N 1 is the transverse momentum associated to the subband, and N is the number of C atoms in a transverse section of the nanotube.

In a metallic nanotube, N = 3M, where n is an integer. There are two gapless bands, characterized by

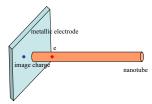


FIG. 1: Sketch of one of the geom etries considered in order to calculate the charge distribution in the nanotube.

n=M. Other bands with $n\in M$ have a gap, n=t] $2\cos(n=2)$ j. Thus, the electronic states of the two bands which cross the Ferm i level can be described by the simple ham iltonian:

$$X$$
 $H = t c_{n,s}^{y} c_{n+1,s} + h.c.$ (1)

The Ferm ivelocity can be written as $v_F=2ta$, where a is the lattice constant. We consider a nite nanotube with L unit cells. When an electron hops into the nanotube its charge will be distributed throughout its length. In a 11st approximation, this charge can be calculated using the Hartree or Hartree-Fock approximation. As the electrostatic potential is weakly screened in a one dimensional geometry, the charge distribution can be in uenced by metallic gates in the vicinity. We 11st consider the setup depicted in Fig.[1], where the electron is emitted from a metallic electrode at one end of the nanotube. More complicated geometries will be studied later.

We consider the two spin degenerate bands which cross the Ferm i level. The polarization of the remaining bands by the potential associated to the charge of a single electron will be small, and it can be treated perturbatively. The radius of the nanotube acts as a short distance cuto of the Coulomb potential. We describe the electrode by an image charge induced by the physical charge on the nanotube. We approximate the electrostatic interaction between electrons located at

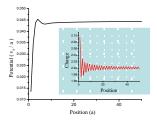


FIG .2: Electrostatic potential and charge (inset) at the edge of a nanotube with an additional electron and L = 1024 unit cells. The parameters used are $e^2 = v_F = 5.4$, R = a = 3 and d=a = 1.

unit cells n_1 and n_2 as measured from the gate, as:

$$V_{\text{tot}}(n_1; n_2) = V_{\text{el}}(n_1 - n_2) \quad V_{\text{el}} \quad n_1 + n_2 + \frac{d}{a}$$

$$V_{\text{el}} \quad n_1 \quad n_2 + \frac{d}{a} + V_{\text{el}}(n_1 + n_2)$$

$$V_{\text{el}}(n) = \frac{e^2}{n^2 a^2 + R^2}$$
 (2)

where d is equal to twice the distance between the nanotube and the electrode, and R is the radius of the nanotube.

Results. The electrostatic potential and the induced charge when the number of electrons in one of the four subbands at the Ferm i level is one above half lling (which is taken as the neutral situation) is shown in Fig.[2].

The calculations have been done using the Hartree approximation. The results are signicantly changed if exchange is included. We not enhanced Friedel oscillations[22], and a sizable gap pinned at the Fermi level. Some of these e ects are due to changes in bulk properties which are unrelated to the addition of electrons. In the following, we present results obtained within the Hartree approximation, where the features associated to single charges are easier to isolate.

A non negligible fraction of the charge is localized by its im age near the electrode. This leads to a reduction of the repulsive electrostatic potential in that region. This e ect is relatively small compared with the gaps of the higher lying subbands of a small carbon nanotube, so that the assumption of neglecting their polarization is

justi ed. W e also $\,$ nd substantial Friedel oscillations, which have periodicity two, as $k_F=\,$ =a.

The charge distribution depends strongly on the location of the external electrodes. Fig.[3] compares the potential calculated previously with the one obtained when there are two symmetrically placed electrodes at each end of the nanotube, and in the absence of electrodes, all other parameters being the same.

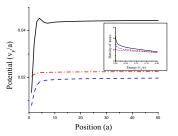


FIG. 3: Electrostatic potential induced by a single electron when there is one electrode (full line), two symmetrically placed electrodes (dashed line), and no electrodes (dashed line). The inset shows the non equilibrium density of states for the same three cases.

The e ects associated with the non homogeneous charge distribution after the injection of a single electron are described, within the Hartree approximation used above, as a change of all electronic levels. Taking this e ect into account, the electronic density of states is changed as: i) The overlap between the initial and -naleigenstates is reduced. In the limit of vanishing level spacing, this leads to the orthogonality catastrophe induced by the sudden switching of a local potential[23]. ii) The potential shifts the electrons towards the electrode, enhancing the density of states at the Ferm i level in its vicinity. This is the so called excitonic e ect [14, 24] and it opposes the orthogonality catastrophe.

The nallocal density of states, in the limit of vanishing level splitting, goes as D (!) / ! [(1 -)^2 - 1] [14], where > 0. Hence, for su ciently small perturbations, < 1, the tunnelling density of states is enhanced at the ends of the nanotube. The elective density of states can be obtained by assuming that the hamiltonian after the charging of the nanotube is modified from an initial expression H $_0$ to H $_{\rm f}$ = H $_0$ + $V_{\rm SC}$, where $V_{\rm SC}$ is the modication of the Hartree-Fock potential induced by the extra electron. Assuming that the tunnelling takes place at position 1 and subband 1 near the edge of the nanotube, the tunnelling density of states at zero temperature is:

$$G(!) = \int_{j_{6},j}^{Y} \mathbf{j}_{j,j} \mathbf{n}_{j} \mathbf{n$$

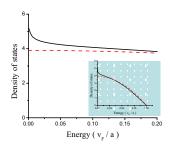


FIG. 4: E ective tunneling density of states at the end of a nanow ire with L=1024 unit cells, using the same parameters as in Fig.[2]. The dotted line is the density of states in the absence of nal state e ects. The inset gives the density of states over the entire bandwidth of the conduction band.

where the states j_i , $N_{(0;f);j}$ are eigenstates of $H_{0;f}^j$ with $N_{(0;f);j}^j$ with $N_{(0;f);j}^j$ are eigenstates of $H_{0;f}^j$ with $N_{(0;f);j}^j$ with $N_{(0;f);j}^j$

Results obtained for the injection in a neutral nanotube with L = 1024 unit cells and the parameters which lead to the electrostatic potentials shown in Fig.[3] are shown in the inset of Fig.[3], and, in more detail, in Fig.[4], where they are also compared with the results obtained neglecting $V_{\rm SC}$.

Luttinger liquid e ects. The calculation discussed above takes into account, in an approxim ateway, the interaction corrections expected at the boundary of a Luttinger liquid. The anomalous exponent in the density of states can be estimated using rst order perturbation theory, and it is nite within Hartree-Fock theory [25]. Note that the calculations also describe approximately the crossover to a Fermi liquid behavior at su ciently high energies [25].

For su ciently long wires, we can use the bosonization approach. The calculation of the nal state e ects leading to eq.(3) can be extended without too much difculty to the case of a Luttinger liquid with forward interactions. The initial and nal bosonized ham iltonians are [26]:

$$H_{0} = \frac{1}{2} \sum_{\substack{x \geq 0 \\ Z}} dx 4 v_{F}^{2}(x) + \frac{v_{F}}{4} [\theta_{x} (x)]^{2} + \frac{e^{2}}{8} \sum_{\substack{x \geq 0 \\ Z}} dx dx dy \theta_{x} (x) V_{tot}(x; y) \theta_{y} (y)$$

$$H_{f} = H_{0} + \frac{1}{2} \int_{x \geq 0} dx V_{sc}(x) \theta_{x} (x)$$
(4)

The ham iltonians H $_{\rm 0}$ and H $_{\rm f}$ di er by a term which is linear in the boson elds, and there is a simple unitary transform ation, U which transform s one into the other. The calcuation of the density of states can be written as

the Fourier transform of the expression:

G (t) =
$$h0j$$
 (x = $0)e^{iH t y}$ (x = $0)j0i$
= $h0j$ (x = $0)U^{-1}e^{iH_0t}U^{-y}$ (x = $0)j0i$ (5)

where \mathfrak{I} i is the ground state of H $_0$, and we are assuming that the end of the nanotube is at position x=0.

The ham iltonians in eq.(4) are quadratic in the boson coordinates, and the expression in eq.(5) can be calculated by normal ordering the operators, which depend exponentially on the bosonic degrees of freedom. If we neglect the breakdown of translational symmetry induced by the gates, and the long range elects of the Coulomb potential, the tunnelling density of states becomes:

D (!) / j!
$$\frac{1}{j}$$
 1 $g^2 \frac{v}{v_F}$ 1 (6)

where g is the parameter which describes the Luttinger liquid properties, and V = are eigenstates of H $_{0;f}^{j}$ with $(2)^{-1}$ lim $_{k!}$ $_{0}^{-1}$ e^{ikx} V_{sc} (x)dx. For repulsive in-4 is the band index. As these teractions, g < 1, and Luttinger liquid e ects tend to suppress the positive anomaly studied here.

In the presence of gates, the electron (electron potential is not translationally invariant. The screening e ects of the gates reduce locally the interactions, which are unscreened away from the gate. A related situation was considered in [27], a Luttinger liquid connected to non interacting gates. The quadratic ham iltonian, eq.(4), which is de ned on a half line, x; y > 0, can be solved by de ning a related problem on the entire axis [28]. We can estimate in a sim ple way the value of the param eter g at the edge of the nanotube from the energy associated to a uctuation of the charge density on a scale 1 < L in that region. This estimate, in the thermodynamic limit, leads to the charge com pressibility and to the bulk value of g. In the absence of screening by gates, the inverse compressibility diverges logarithm ically with the size of the system. It is easy to show that, in the geometry depicted in Fig.[1], the energy associated to a uctuation of size 1 is given by a term which diverges logarithmically as 1! 1 minus a term which tends to a constant. The second term describes the screening e ects of the gate. Thus, for large nanotubes and at su ciently low energies, bulk e ects determ ine the value of g, and the tunnelling density of states will be given by eq.(6). At high energies, on the other hand, the screening of the electron (electron interactions by the gate makes g! 1 and the non equilibrium e ects described here will dominate. The crossover between these two regim es depends on the lim iting value of the interaction, which, in turn, is in uenced by screening by other parts of the system (see below).

Single electron properties. At su ciently low energies or temperatures, a nite nanotube behaves like a quantum dot[1, 2, 6, 7, 8, 9, 29, 30]. For the parameters used here, $e^2 = v_F = 5.4$, the level splitting and the charging energy are comparable. The Hartree calculation described above allows us to estimate the charging energy, $E_C = E_{N+1} + E_{N-1} - 2E_N$. The Coulomb potential considered here, in the absence of gates, leads

to E $_{\rm C}$ e²L 1 log (L=R). The screening by the vertical gates, as in F ig.[1], reduces this value by a quantity which scales as L 1 . For the param eters used in F ig.[2] we nd a level spacing (in units of $v_{\rm F}$ =a) of E = 0:00306, and a charging energy E $_{\rm C}$ = 0:0196.

The nal state e ects considered here manifest them selves, at the scale of the level spacing, as a dependence of the tunnelling amplitude on the charge state. This e ect can be included by adding assisted hopping terms to the ham iltonian [31, 32, 33] (see also [34]). This e ect, in our case, is rather small. Using the parameters in Fig.[2], the value of the square of the renormalized creation operator (see eq.(3)) at zero energy is 0.002616 for the transition $N \cdot N + 1$ and 0.002612 for $N + 1 \cdot N + 2$ (note that these transitions involve the same electronic level). The smallness of the nal state e ects on single particle levels shows that the enhancement of the ective tunnelling of states is a collective phenomenon, which arises from the cumulative changes in many levels near the Fermienergy.

Conclusions. We have analyzed, sem is quantitatively, the appearance of a low energy peak in the tunnelling of states in nanotubes due to the inhom ogeneous potential induced by the charge of a single electron. This zero bias anomaly is closely related to the excitonic resonance which appears in X-ray absorption in metals[14, 24]. The formation of this resonance enhances the tunnelling den-

sity of states, although it is induced by the Coulomb interaction. The strength of this anomaly depends on the screening of the nanotube by metallic contacts and gates, and, presumably, it can be tuned experimentally.

The strength of the enhancement of the tunnelling density of states can be suppressed by Luttinger liquid effects, for repulsive electron (electron interactions. Luttinger liquid e ects are reduced when the interaction is screened, which, on the other hand, favors the existence of the excitonic resonance. The e ects discussed here should also be present in multiwall nanotubes. In a system with many bands at the Fermi level, only one contributes to the resonance, while the others induce an orthogonality catastrophe (note that we have considered four bands here, see eq.(3)).

The presence of an excitonic resonance makes the transport properties of the nanotube sim ilar to those of Luttinger liquids with attractive interactions. It can lead to the enhancement of the proximity election in anotubes attached to superconducting electrodes [35, 36, 37], and increase, in general, the tendency towards superconductivity in these system s[38].

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